



Form 1449*

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT
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Atty. Docket No.: 303.378JIS1

Serial No. 08/903.453

Sheet 1 of 7

Applicant: Leonard Forbes et al

Filing Date: July 29, 1997

Filing Date: July 29, 1997

Group: 1104

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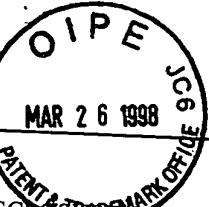
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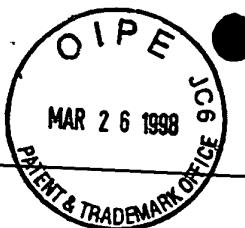
V. Martin Wolfe

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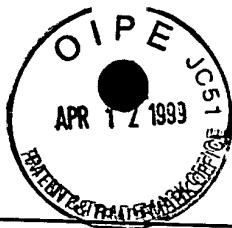
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